

SMD Schottky Barrier Diode

COMCHIP
SMD Diodes Specialist

CDBF0130 (Lead-free Device)

I_o = 100 mA

V_R = 30 Volts



Features

Designed for mounting on small surface.

Extremely thin/leadless package.

Low drop-down voltage.

Majority carrier conduction.

Mechanical data

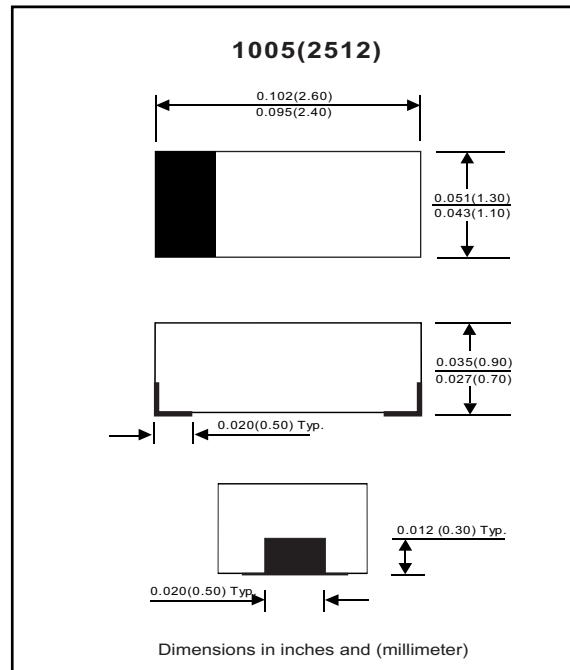
Case: 1005 (2512) Standard package , molded plastic.

Terminals: Gold plated, solderable per MIL-STD-750, method 2026.

Polarity: Indicated by cathode band.

Mounting position: Any.

Weight: 0.006 gram (approximately).



Maximum Rating (at T_A = 25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Repetitive peak reverse voltage		V _{RRM}			35	V
Reverse voltage		V _R			30	V
Average forward current		I _o			100	mA
Forward current , surge peak	8.3 ms single half sine-wave superimposed on rate load (JEDEC method)	I _{FSM}		1000		mA
Power Dissipation		P _D			250	mW
Storage temperature		T _{TG}	-40		+125	°C
Junction temperature		T _j	-40		+125	°C

Electrical Characteristics (at T_A = 25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	I _F = 100 mA DC	V _F			0.44	V
Reverse current	V _R = 30 V	I _R			30	uA
Capacitance between terminals	f = 1MHz, and 10 VDC reverse voltage	C _T		9		pF

RATING AND CHARACTERISTIC CURVES (CDBF0130)

Fig. 1 - Forward characteristics

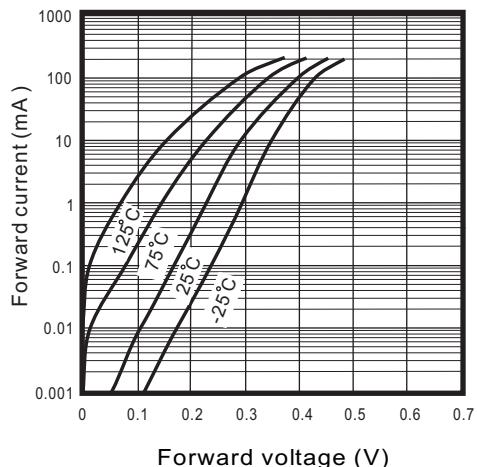


Fig. 2 - Reverse characteristics

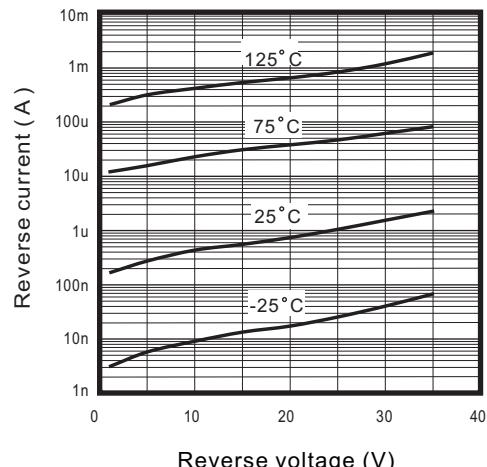


Fig. 3 - Capacitance between terminals characteristics

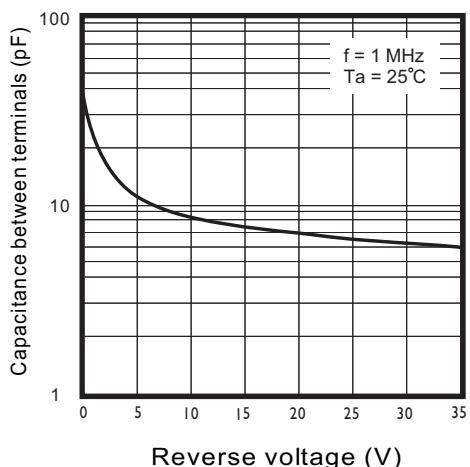


Fig. 4 - Current derating curve

